AMENDMENTS

In the Claims

41. (Twice Amended) A semiconductor processing method of forming a conductive transistor gate over a substrate comprising [the steps of]:

forming a conductive gate electrode over a gate dielectric layer on a substrate, the gate electrode having sidewalls and an interface with the gate dielectric layer;

forming sidewall spacers comprising nitride over the [gate's] gate electrode's sidewalls, the sidewall spacers joining with the gate dielectric layer; and

after forming the sidewall spacers comprising nitride, exposing the substrate to oxidizing conditions effective to channel oxidants through the gate dielectric layer and underneath the sidewall spacers joined therewith, wherein [only] a portion of the gate electrode, laterally adjacent the sidewall spacers and at the interface with the gate dielectric layer, is oxidized.

Cancel Claim 42 without prejudice.

45. (Twice Amended) A semiconductor processing method of forming a conductive gate comprising:

forming a conductive gate structure on a first layer which is disposed on a substrate, the gate structure comprising a gate electrode having sidewalls and an interface with the first layer;

forming sidewall spacers [over] laterally adjacent the conductive [gate's] gate structure's sidewalls sufficiently to cover all conductive material comprising the sidewalls, the sidewall spacers comprising an oxidation resistant material; and

after forming the oxidation resistant sidewall spacers, conducting an oxidizing step by channeling oxidants through the first layer which is outwardly exposed laterally proximate the oxidation resistant sidewall spacers wherein the oxidation resistant sidewall spacers provide that only a portion of the gate electrode, adjacent the oxidation resistant sidewall spacers and at the interface with the first layer, is oxidized.

47. (Amended) The method of claim 45, wherein the gate stack comprises a polysilicon layer, an overlying metal layer, and an electrically conductive reaction barrier layer intermediate the polysilicon layer and the overlying metal layer.

In Claim 48, at line 3 of the claim, insert --stack-- immediately after "gate."

and at line 6 of the claim, replace "gate's" with --gate stack's--.

In Claim 49, at lines 3 and 5 of the claim, insert --stack-- immediately after "gate."

50. (Twice Amended) A semiconductor processing method of forming a conductive transistor gate over a substrate comprising:

forming a dielectric layer on a substrate;

forming a conductive gate structure over the dielectric layer, the gate structure having sidewalls defining a lateral dimension of the gate structure;

forming non-oxide material over the gate structure and the dielectric layer [adjacent the gate];

anisotropically etching the non-oxide material to form [non-oxide] spacers over the sidewalls, the spacers laterally adjacent the gate structure and joining with the gate dielectric layer there at [adjacent the gate]; and

after forming the spacers, exposing the substrate to oxidizing conditions effective to oxidize only that portion of the gate structure adjacent [proximate] the spacers and the dielectric layer.